



General Description

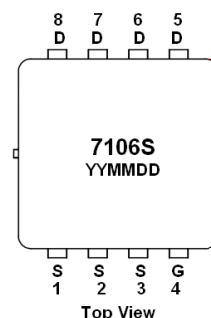
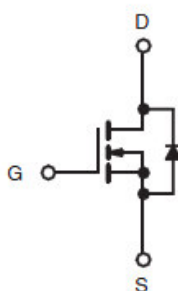
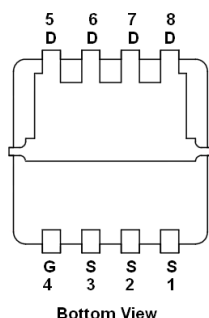
AFN7106S, N-Channel enhancement mode MOSFET, uses Advanced Trench Technology to provide excellent $R_{DS(ON)}$, low gate charge.

These devices are particularly suited for low voltage power management, such as smart phone and notebook computer and other battery powered circuits, and low in-line power loss are needed in commercial industrial surface mount applications.

Features

- 20V/20A, $R_{DS(ON)}=6.2m\Omega@V_{GS}=4.5V$
- 20V/15A, $R_{DS(ON)}=8.4m\Omega@V_{GS}=2.5V$
- Super high density cell design for extremely low $R_{DS(ON)}$
- Exceptional on-resistance and maximum DC current capability
- DFN3.3X3.3-8L package design

Pin Description (DFN3.3X3.3-8L)



Application

- DC-DC Converter
- POL

Pin Define

Pin	Symbol	Description
1	S	Source
2	S	Source
3	S	Source
4	G	Gate
5	D	Drain
6	D	Drain
7	D	Drain
8	D	Drain

Ordering Information

Part Ordering No.	Part Marking	Package	Unit	Quantity
AFN7106SFN308RG	7106S	DFN3.3X3.3-8L	Tape & Reel	5000 EA

※ YY year code

※ MM month code

※ DD date code

※ AFN7106SFN308RG : 13" Tape & Reel ; Pb- Free ; Halogen- Free



Absolute Maximum Ratings

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Typical	Unit
Drain-Source Voltage	V _{DSS}	20	V
Gate –Source Voltage	V _{GSS}	±12	V
Continuous Drain Current(T _J =150°C)	I _D	20	A
		15	
Pulsed Drain Current	I _{DM}	70	A
Continuous Source Current(Diode Conduction)	I _S	40	A
Power Dissipation	P _D	3.8	W
		2	
Operating Junction Temperature	T _J	150	°C
Storage Temperature Range	T _{STG}	-55/150	°C
Thermal Resistance-Junction to Ambient	R _{θJA}	120	°C/W

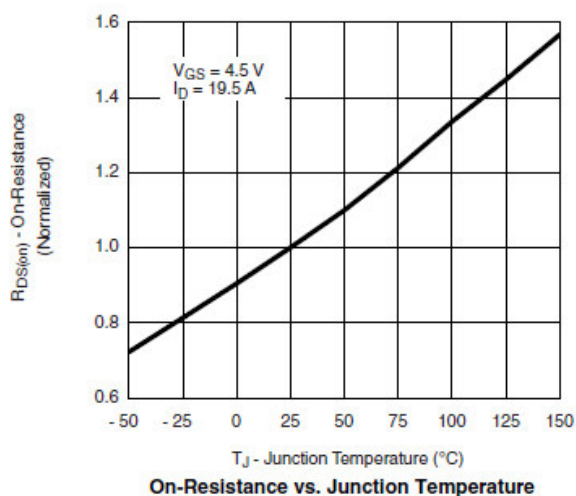
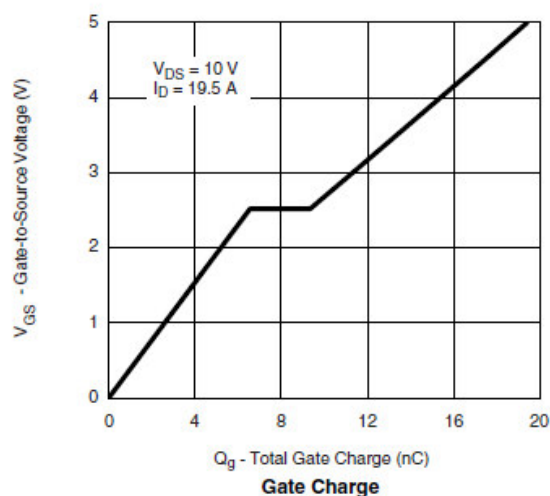
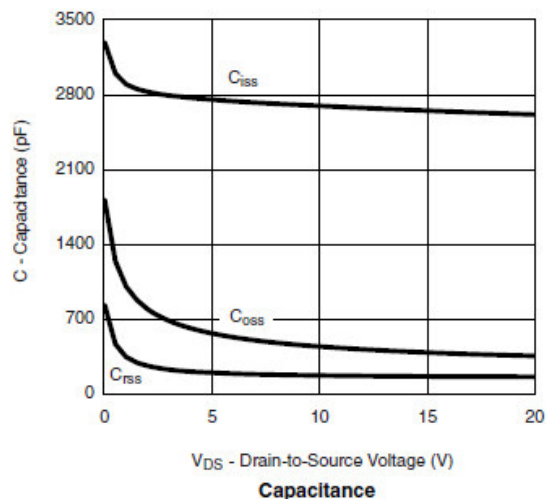
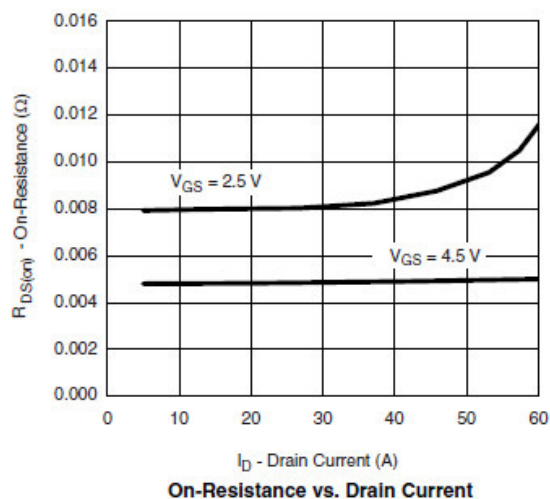
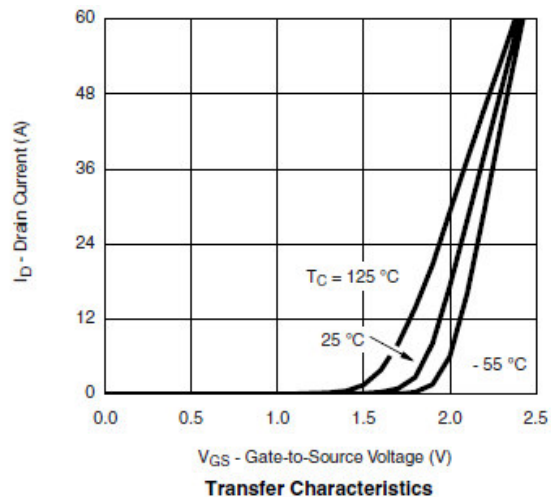
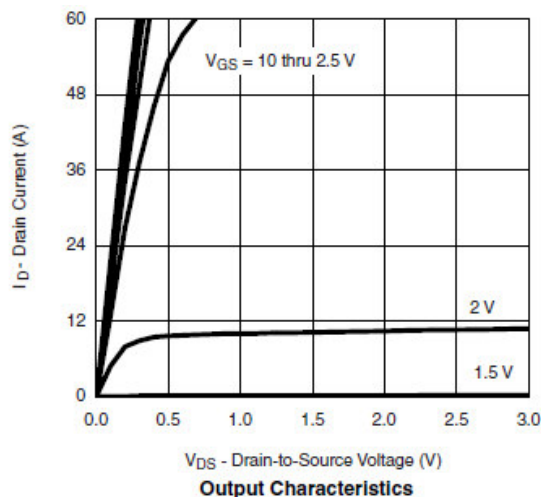
Electrical Characteristics

(T_A=25°C Unless otherwise noted)

Parameter	Symbol	Conditions	Min.	Typ	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} =0V, I _D =250uA	20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	0.5		1.0	
Gate Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =16V, V _{GS} =0V			1	uA
		V _{DS} =16V, V _{GS} =0V T _J =85°C			10	
On-State Drain Current	I _{D(on)}	V _{DS} ≥5V, V _{GS} =4.5V	50			A
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} =4.5V, I _D =20A		4.3	6.2	mΩ
		V _{GS} =2.5V, I _D =15A		5.5	8.4	
Forward Transconductance	g _{FS}	V _{DS} =15V, I _D =20 A		80		S
Diode Forward Voltage	V _{SD}	I _S =3.2A, V _{GS} =0V		0.7	1.3	V
Dynamic						
Total Gate Charge	Q _g	V _{DS} =10V, V _{GS} =4.5V I _D ≡20A		15	25	nC
Gate-Source Charge	Q _{gs}			6		
Gate-Drain Charge	Q _{gd}			5		
Input Capacitance	C _{iss}	V _{DS} =15V, V _{GS} =0V f=1MHz		1800		pF
Output Capacitance	C _{oss}			350		
Reverse Transfer Capacitance	C _{rss}			150		
Turn-On Time	t _{d(on)}	V _{DD} =10V, R _L =10Ω I _D ≡1A, V _{GEN} =10V R _G =6.0Ω		25	40	ns
	t _r			15	25	
Turn-Off Time	t _{d(off)}			50	75	
	t _f			15	25	

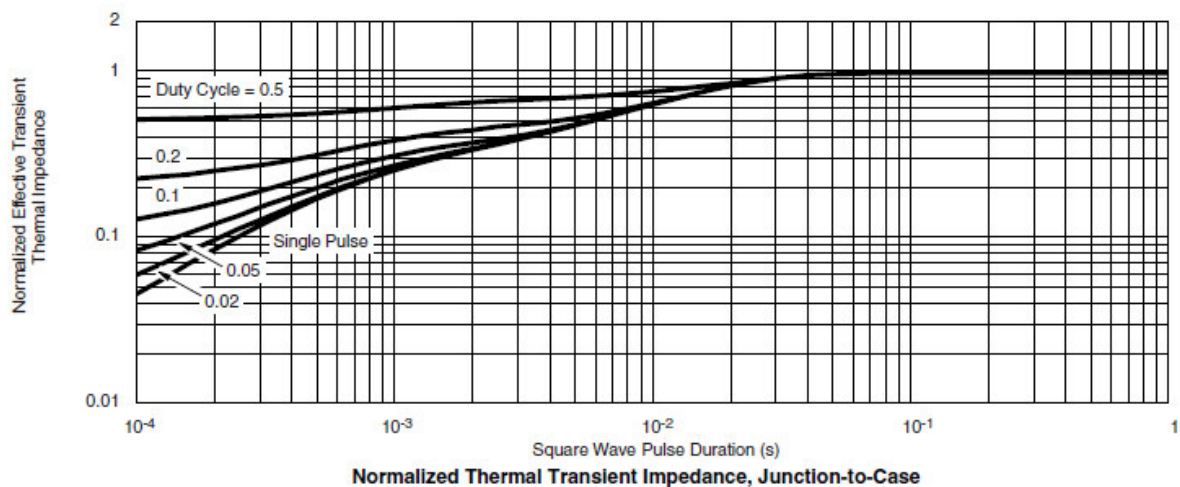
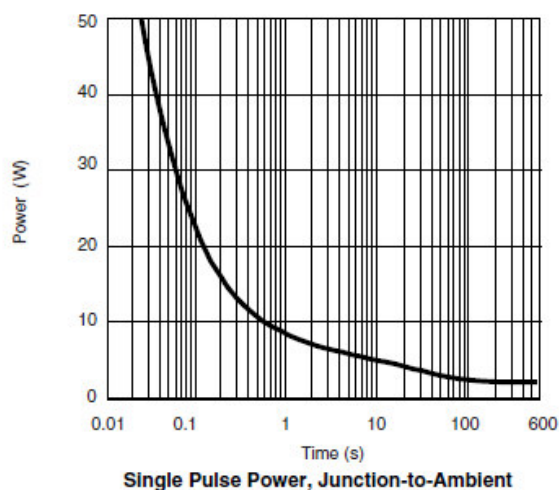
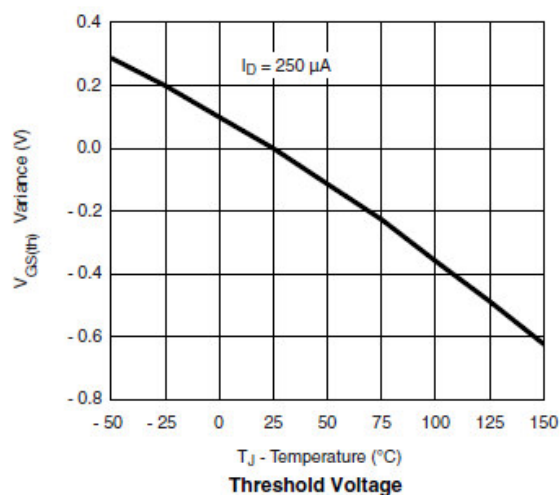
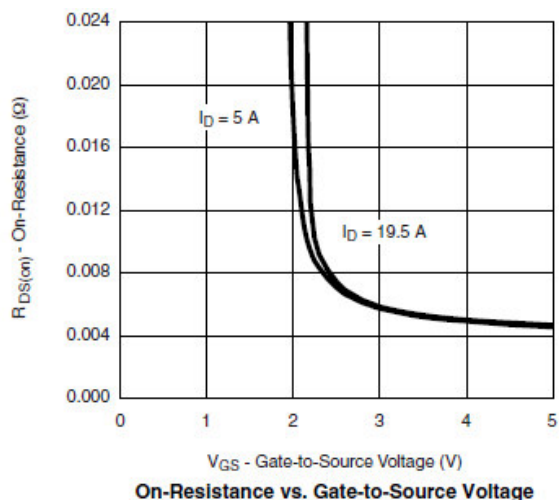
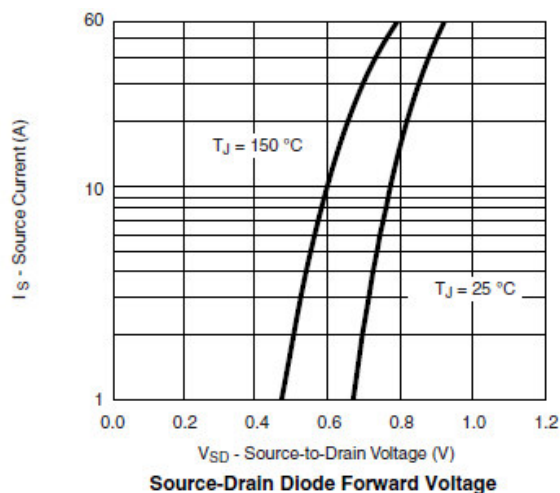


Typical Characteristics





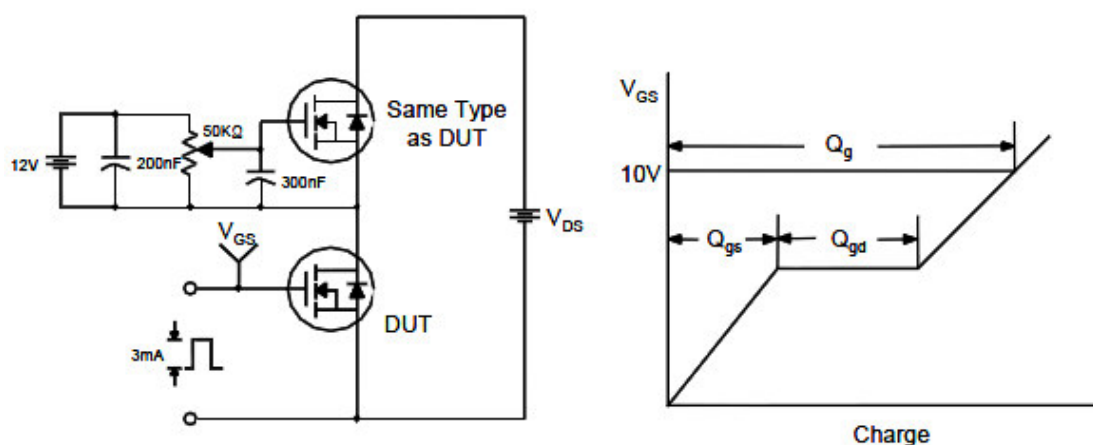
Typical Characteristics



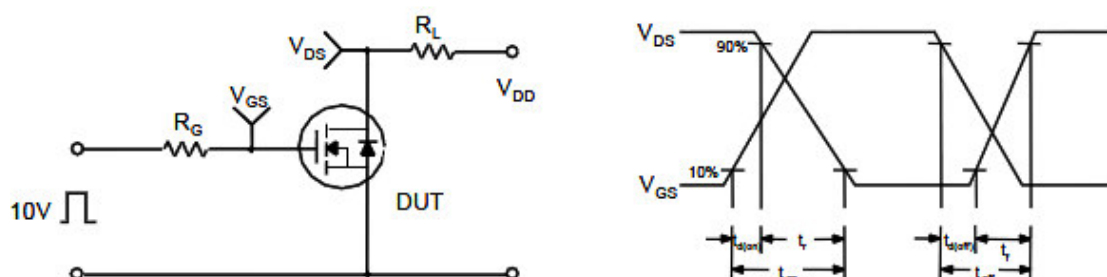


Typical Characteristics

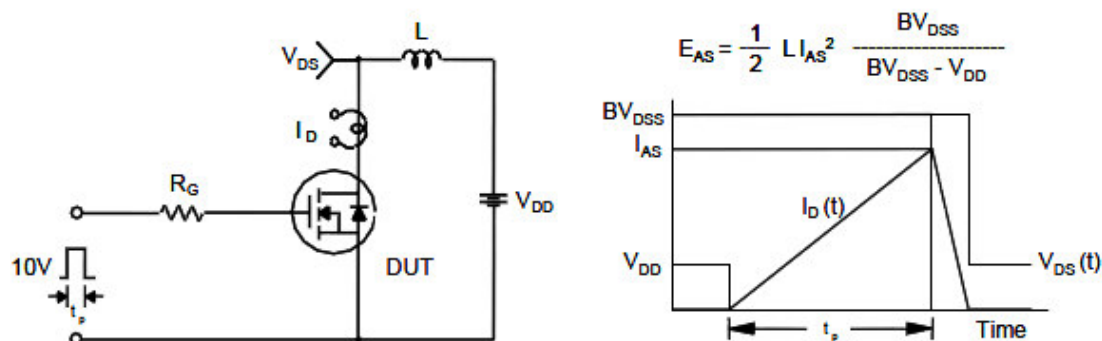
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms

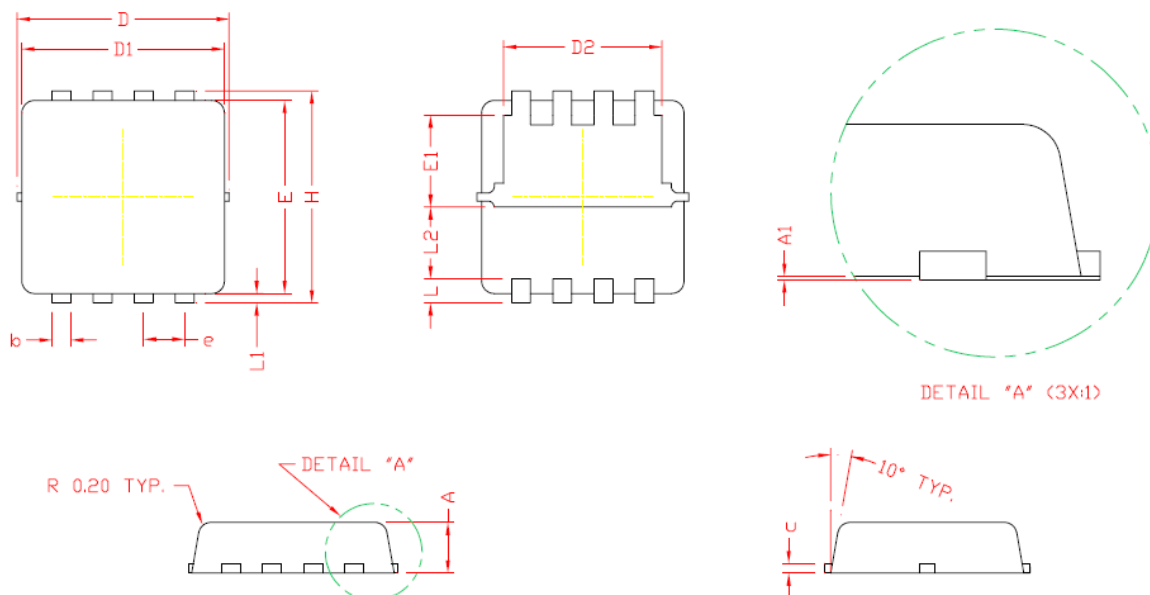


Unclamped Inductive Switching Test Circuit & Waveforms





Package Information (DFN3.3X3.3-8L)



DIMENSIONS

REF.	Millimeters		REF.	Millimeters	
	Min.	Max.		Min.	Max.
A	0.70	0.90	E	3.00	3.20
A1	0.00	0.05	E1	1.35	1.55
b	0.24	0.35	e	0.65 BSC.	
c	0.10	0.20	H	3.20	3.40
D	3.25	3.40	L	0.30	0.50
D1	3.05	3.25	L1	0.10	0.20
D2	2.40	2.60	L2	1.13 Ref.	

©2010 Alfa-MOS Technology Corp.
 2F, No.80, Sec.1, Cheng Kung Rd., Nan Kang Dist., Taipei City 115, Taiwan (R.O.C.)
 Tel : 886 2) 2651 3928
 Fax : 886 2) 2786 8483
 ©http://www.alfa-mos.com